

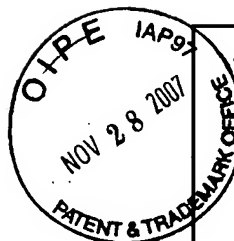


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<b>Substitute for form 1449/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			<b>Complete if Known</b>		
			Application Number	10/581,797 – Conf. # 4944	
			Filing Date	June 2, 2006	
			First Named Inventor	Yang Yang	
			Art Unit	2818	
			Examiner Name	Long K. Tran	
Sheet	1	of	6	Attorney Docket Number	58086-231274

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
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		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
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	B2	WO 02/37500 A1	05-10-2002	The Regents of the University of California		
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NON PATENT LITERATURE DOCUMENTS			
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